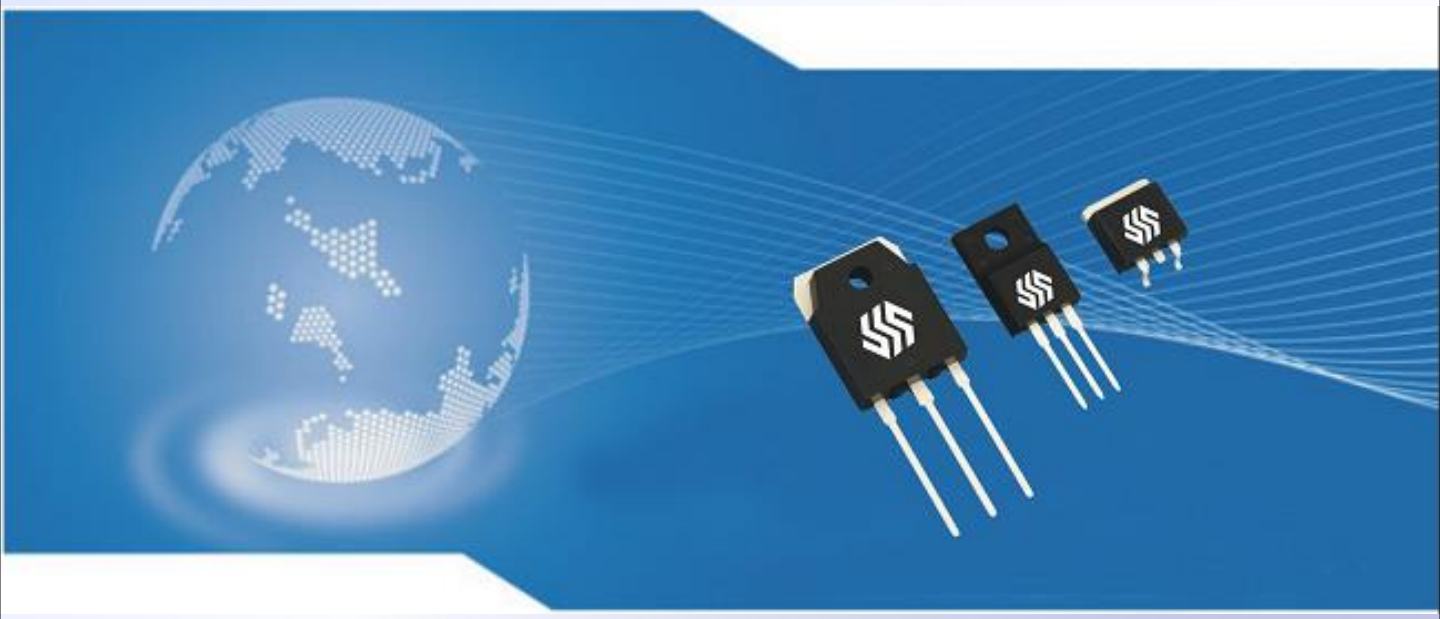
SUPER-SEMI



SUPER-MOSFET

Super Junction Metal Oxide Semiconductor Field Effect Transistor

800V Super Junction Power MOSFET
SS*80R240S

Rev. 1.3
Aug. 2019

www.supersemi.com.cn

SUPER

September, 2013

SJ-FET

SSW80R240S/SSA80R240S
800V N-Channel MOSFET

Description

SJ-FET is new generation of high voltage MOSFET family that is utilizing an advanced charge balance mechanism for outstanding low on-resistance and lower gate charge performance.
This advanced technology has been tailored to minimize conduction loss, provide superior switching performance, and withstand extreme dv/dt rate and higher avalanche energy.
SJ-FET is suitable for various AC/DC power conversion in switching mode operation for higher efficiency.

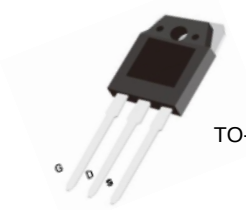
Features

- Multi-Epi process SJ-FET
- 850V @TJ = 150 ℃
- Typ. RDS(on) = 0.22Ω
- Ultra Low Gate Charge (typ. Qg = 27.5nC)
- 100% avalanche tested

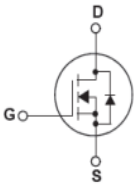
SSW80R240S

TO-247

SSA80R240S



TO-3P



Absolute Maximum Ratings

Symbol	Parameter	SSW_A80R240S	Unit
V_{DSS}	Drain-Source Voltage	800	V
I_D	Drain Current -Continuous (TC = 25℃) -Continuous (TC = 100℃)	 18.4* 11.6*	A
I_{DM}	Drain Current – Pulsed (Note 1)	51*	A
V_{GSS}	Gate-Source voltage	±30	V
E_{AS}	Single Pulsed Avalanche Energy (Note 2)	485	mJ
I_{AR}	Avalanche Current (Note 1)	3.5	A
E_{AR}	Repetitive Avalanche Energy (Note 1)	1	mJ
dv/dt	Peak Diode Recovery dv/dt (Note 3)	15	V/ns
dVds/dt	Drain Source voltage slope (Vds=640V)	50	V/ns
P_D	Power Dissipation (TC = 25℃)	151	W
T_J, T_{STG}	Operating and Storage Temperature Range	-55 to +150	℃
T_L	Maximum Lead Temperature for Soldering Purpose,1/8” from Case for 5 Seconds	300	℃

* Drain current limited by maximum junction temperature. Maximum duty cycle D=0.75.

Thermal Characteristics

Symbol	Parameter	SSW_A80R240S	Unit
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case	0.83	℃/W
$R_{\theta CS}$	Thermal Resistance, Case-to-Sink Typ.	0.5	℃/W
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	62	℃/W

Electrical Characteristics TC = 25℃ unless otherwise noted

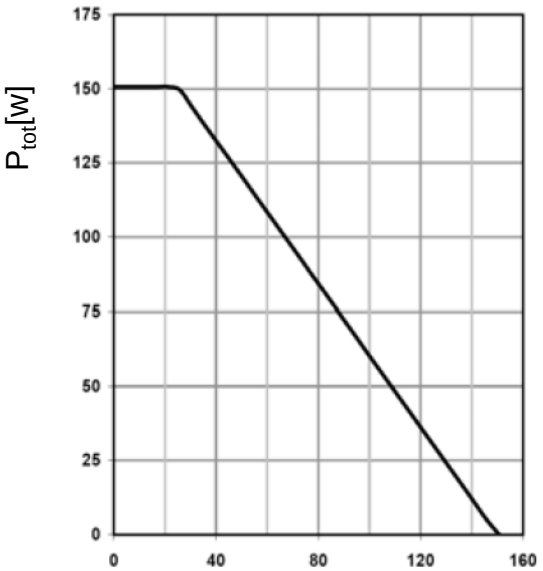
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Off Characteristics						
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS} = 0V, I_D = 250μA, T_J = 25℃	800	-	-	V
		V_{GS} = 0V, I_D = 250μA, T_J = 150℃	-	850	-	V
ΔBV_{DSS} / Δ_{TJ}	Breakdown Voltage Temperature Coefficient	I_D = 250μA, Referenced to 25℃	-	0.6	-	V/℃
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS} = 800V, V_{GS} = 0V -T_J = 150℃	-	- 10	1 -	μA μA
I_{GSSF}	Gate-Body Leakage Current, Forward	V_{GS} = 30V, V_{DS} = 0V	-	-	100	nA
I_{GSSR}	Gate-Body Leakage Current, Reverse	V_{GS} = -30V, V_{DS} = 0V	-	-	-100	nA
On Characteristics						
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS} = V_{GS}, I_D = 250μA	2.5	3.5	4.5	V
$R_{DS(on)}$	Static Drain-Source On-Resistance	V_{GS} = 10V, I_D = 9A	-	0.22	0.26	Ω
g_{FS}	Forward Trans conductance	V_{DS} = 40V, I_D = 18A	-	19	-	S
Dynamic Characteristics						
C_{iss}	Input Capacitance	V_{DS} = 25V, V_{GS} = 0V, f = 1MHz	-	1290	-	pF
C_{oss}	Output Capacitance		-	380	-	pF
C_{rss}	Reverse Transfer Capacitance		-	22	-	pF
Switching Characteristics						
$t_{d(on)}$	Turn-On Delay Time	V_{DD} = 400V, I_D = 10A R_G = 25Ω(Note 4)	-	40	-	ns
t_r	Turn-On Rise Time		-	21	-	ns
$t_{d(off)}$	Turn-Off Delay Time		-	139	-	ns
t_f	Turn-Off Fall Time		-	21	-	ns
Q_g	Total Gate Charge	V_{DS} = 450V, I_D = 10A V_{GS} = 10V (Note 4)	-	27.5	-	nC
Q_{gs}	Gate-Source Charge		-	6.3	-	nC
Q_{gd}	Gate-Drain Charge		-	11.2	-	nC
Drain-Source Diode Characteristics and Maximum Ratings						
I_S	Maximum Continuous Drain-Source Diode Forward Current		-	-	18	A
I_{SM}	Maximum Pulsed Drain-Source Diode Forward Current		-	-	51	A
V_{SD}	Drain-Source Diode Forward Voltage	V_{GS} = 0V, I_F = 20A	-	1	1.5	V
t_{rr}	Reverse Recovery Time	V_R = 400V, VGS = 0V, I_F = 20A, dI_F/dt =100A/μs	-	710	-	ns
Q_{rr}	Reverse Recovery Charge		-	13	-	μC
I_{rrm}	Peak reverse recovery Current		-	33	-	A

NOTES:

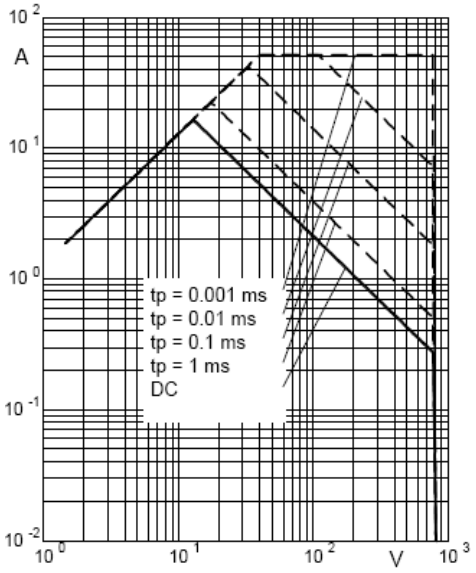
1. Repetitive Rating: Pulse width limited by maximum junction temperature
2. I_{AS}=3.5A, V_{DD}=50V, Starting TJ=25 ℃
3. I_{SD}≤ID, di/dt ≤ 200A/us, V_{DD} ≤ BV_{DSS}, Starting TJ = 25 ℃
4. Essentially Independent of Operating Temperature Typical Characteristics

Typical Performance Characteristics

Power dissipation

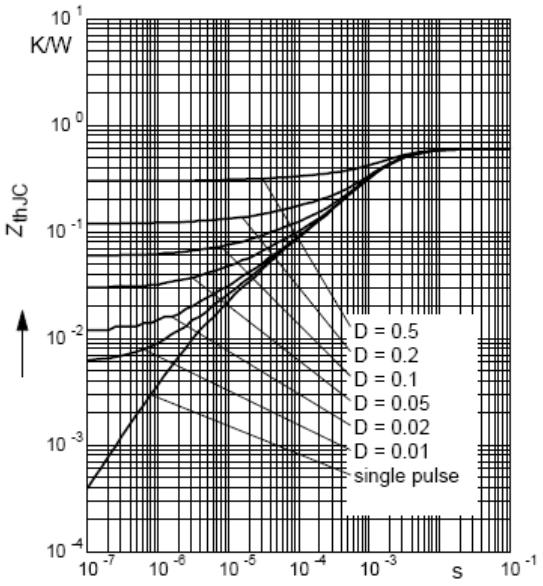


Safe operating area *TC=25* ℃

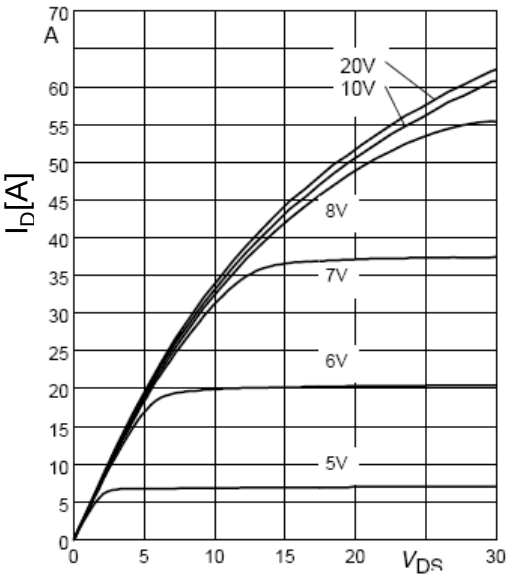


I_D=f(V_{DS}); V_{GS} > 7V; D=0; parameter t_p

Max. transient thermal impedance



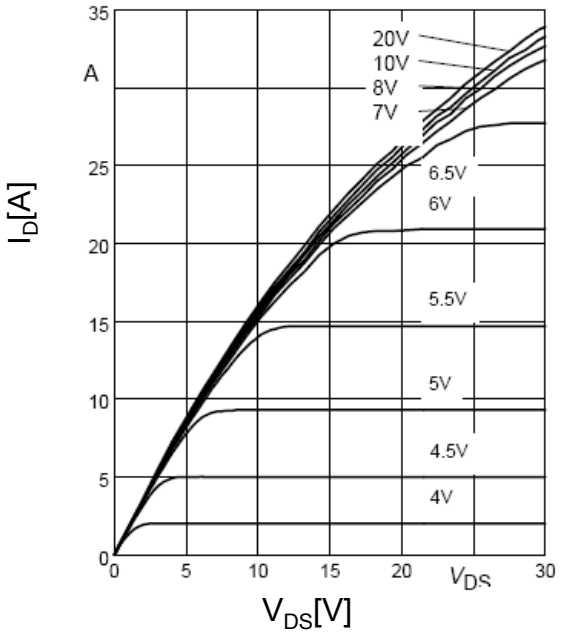
Typ. output characteristics T_j=25 ℃



I_D=f(V_{DS}); T_j=25 ℃ ; parameter: V_{GS}

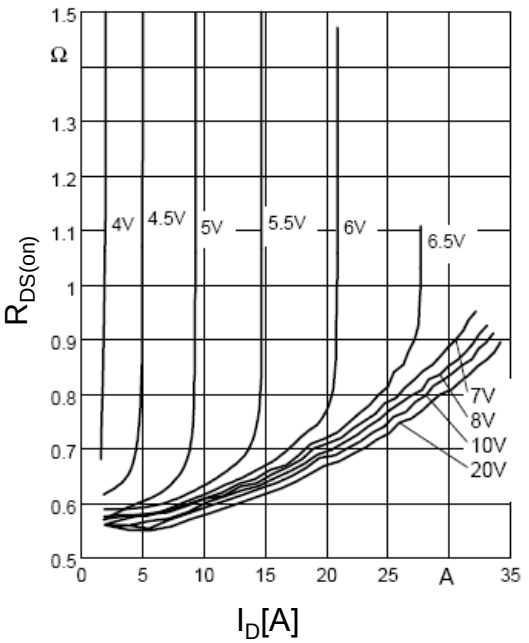
Typical Performance Characteristics

Typ. output characteristics



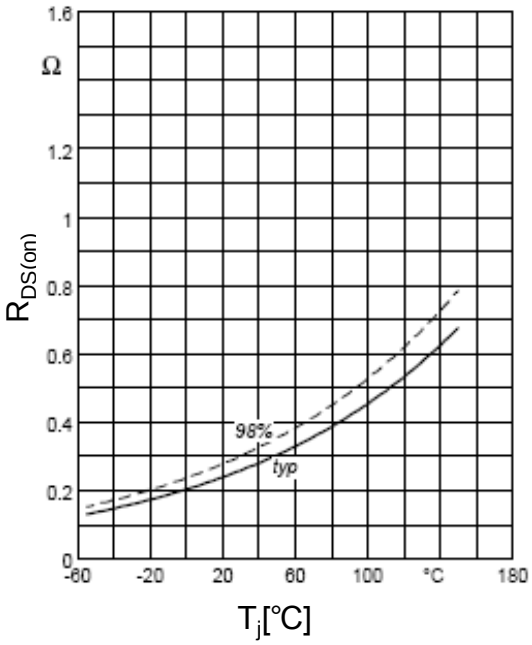
I_D=f(V_{DS}); T_j=150 ℃ ; parameter: V_{GS}

Typ. drain-source on-state resistance



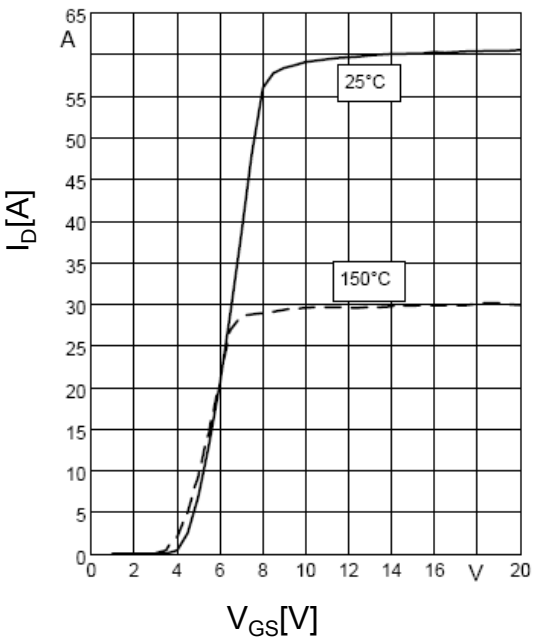
R_{DS}(on)=f(I_D); T_j=150 ℃ ; parameter:V_{GS}

Typ. drain-source on-state resistance



R_{DS}(on)=f(T_j); I_D=11 A; V_{GS}=10 V

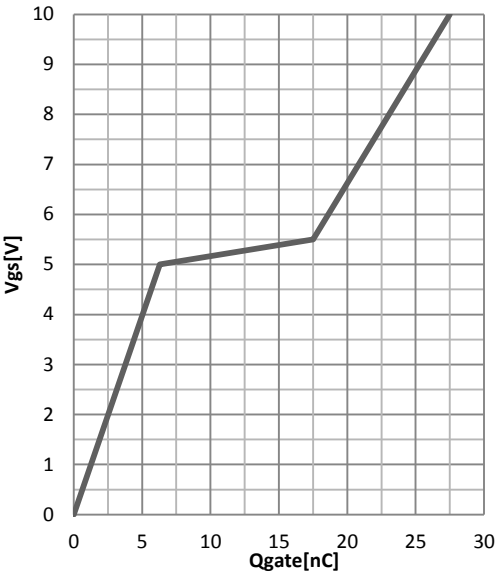
Typ. transfer characteristics



I_D=f(V_{GS}); V_{DS}=40V

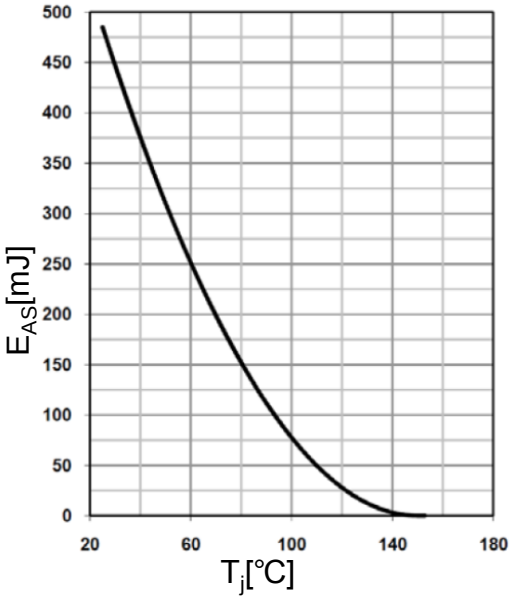
Typical Performance Characteristics

Typ. gate charge



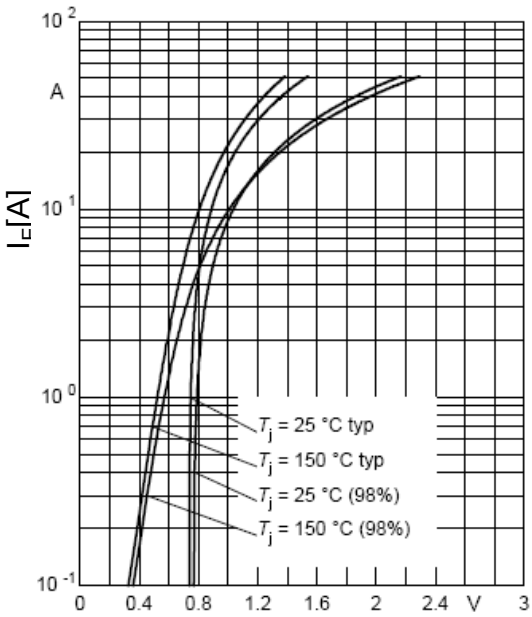
$V_{GS}=f(Q_g)$, I_D=18 A pulsed

Avalanche energy



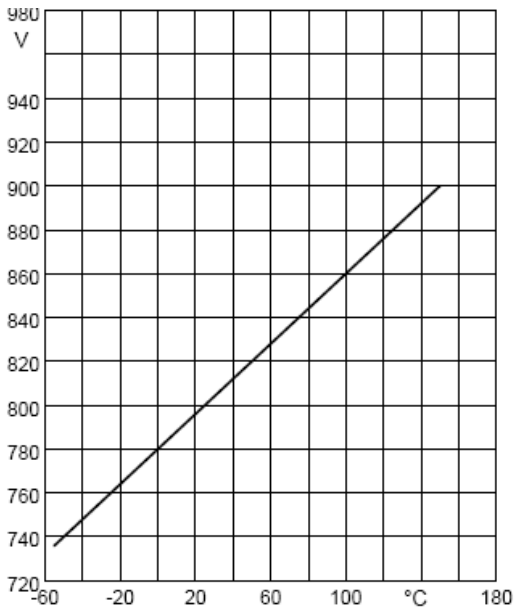
$E_{AS}=f(T_j)$; I_D=3.5 A; V_{DD}=50 V

Forward characteristics of reverse diode



$I_F=f(V_{SD})$; parameter: T_j

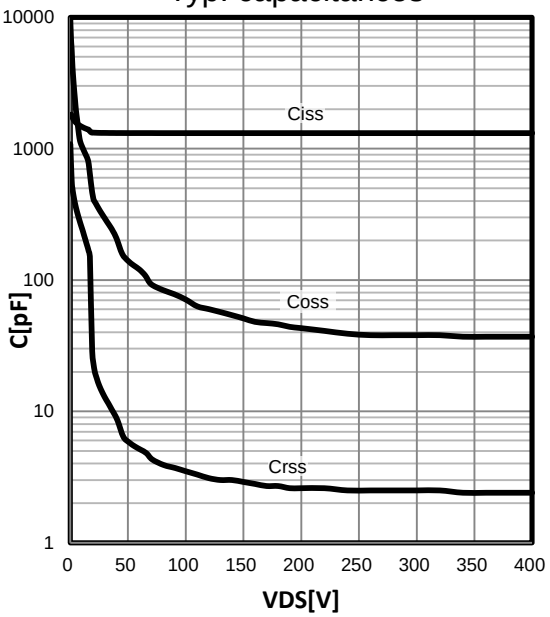
Drain-source breakdown voltage



$V_{BR(DSS)}=f(T_j)$; I_D=1.0 mA

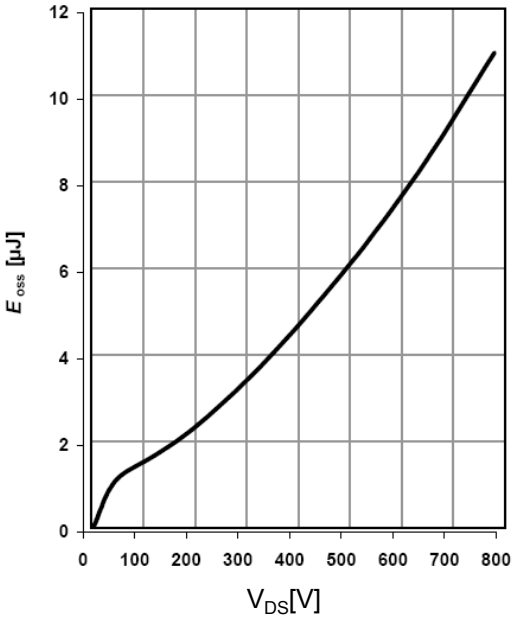
Typical Performance Characteristics

Typ. capacitances



C=f(V_{DS}); V_{GS}=0 V; f=1 MHz

Typ. *Coss stored energy*

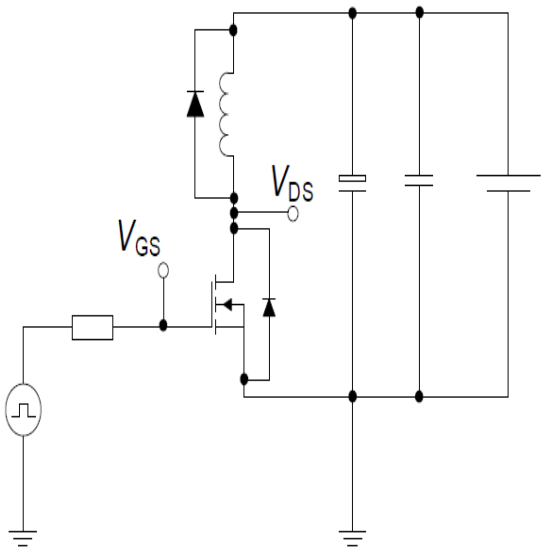


E_{OSS}=f(V_{DS})

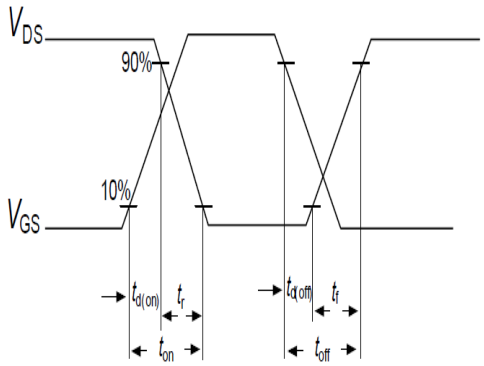
Test circuits

Switching times test circuit and waveform for inductive load

Switching times test circuit for inductive load

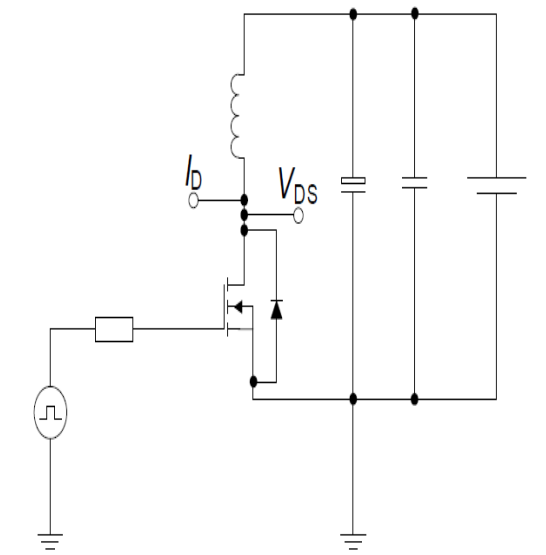


Switching time waveform

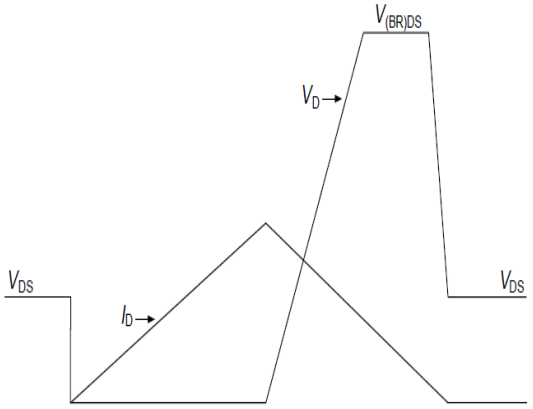


Unclamped inductive load test circuit and waveform

Unclamped inductive load test circuit



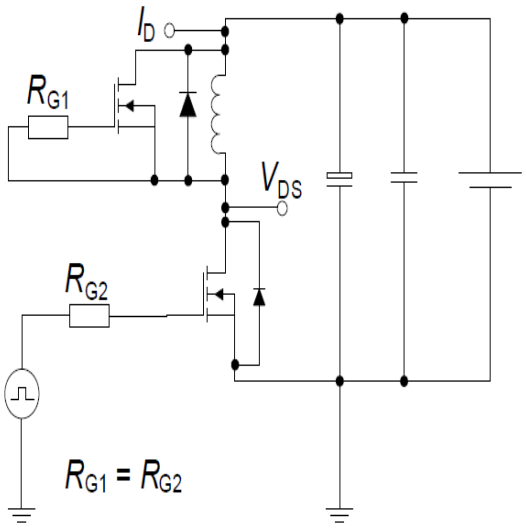
Unclamped inductive waveform



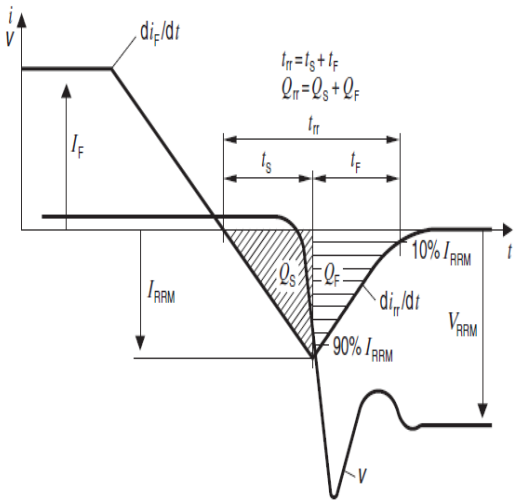
Test circuits

Test circuit and waveform for diode characteristics

Test circuit for diode characteristics

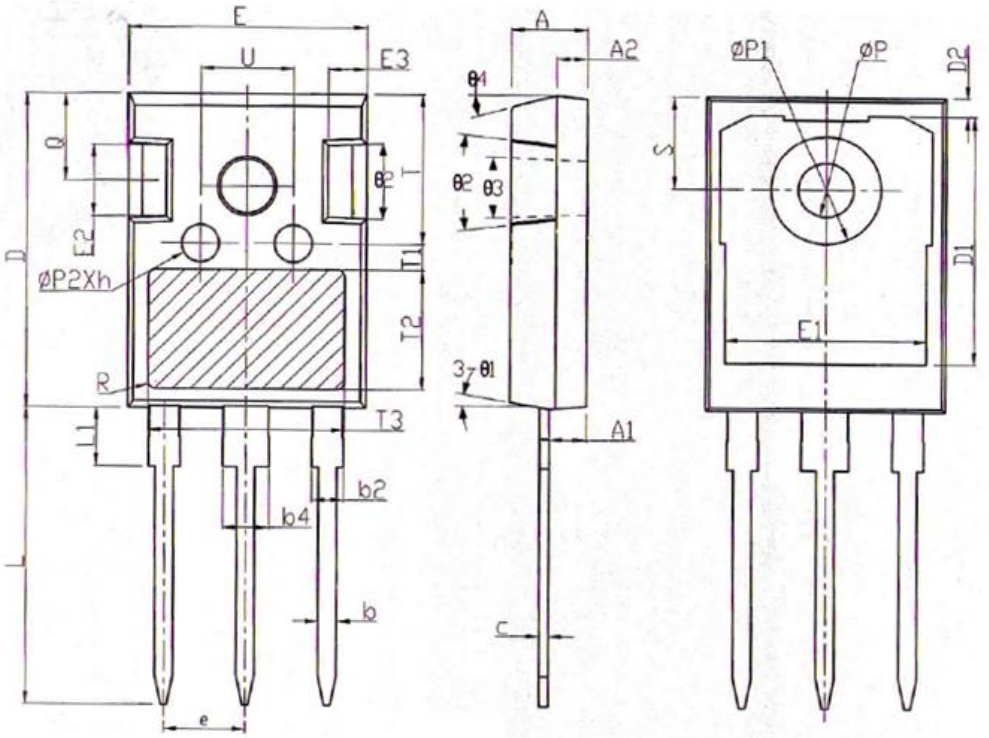


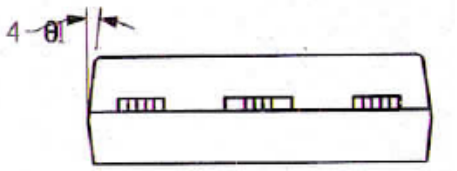
Diode recovery waveform



Package Outline

TO-247



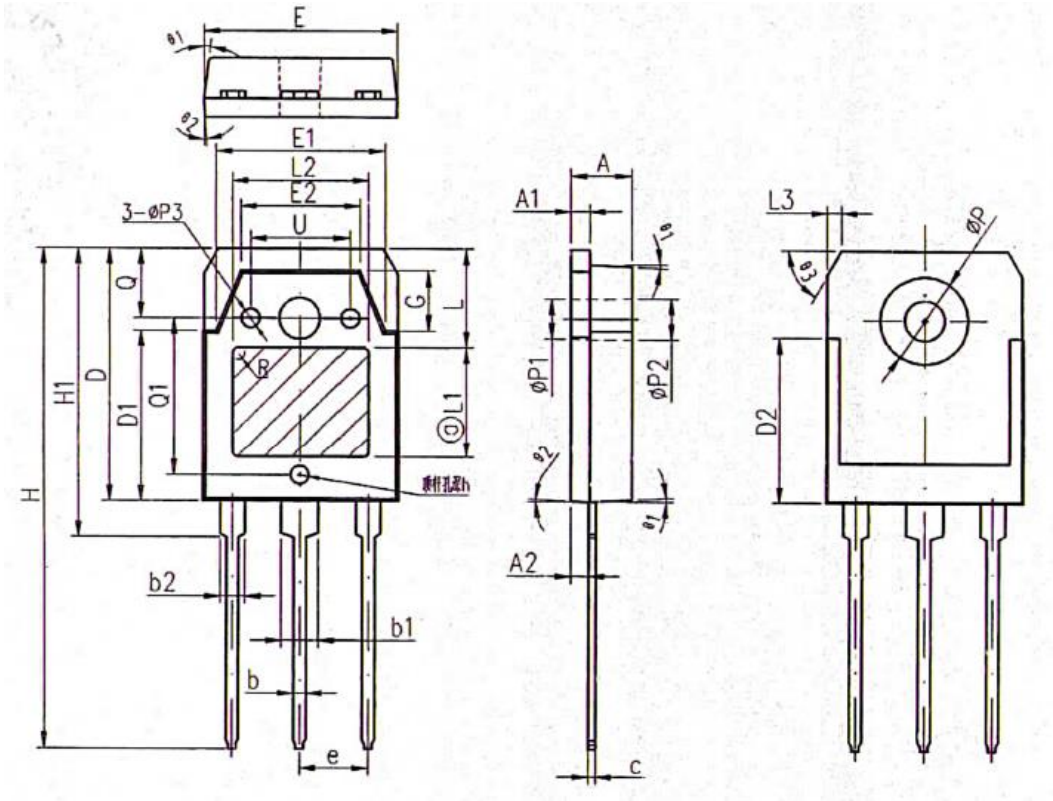


COMMON DIMENSIONS

SYMBOL	MM		
	MIN	NOM	MAX
A	4.90	5.00	5.10
A1	2.31	2.41	2.51
A2	1.90	2.00	2.10
b	1.16	1.21	1.26
b2	1.96	2.01	2.06
b4	2.96	3.01	3.06
c	0.59	0.61	0.66
D	20.90	21.00	21.10
D1	16.25	16.55	16.85
D2	1.05	1.20	1.35
E	15.70	15.80	15.90
E1	13.10	13.30	13.50
E2	4.90	5.00	5.10
E3	2.40	2.50	2.60
e		5.44BSC	
h	0.05	0.10	0.15
L	19.80	19.92	20.10
L1	-	-	4.30
ΦP	3.50	3.60	3.70
ΦP1	-	-	7.30
ΦP2	2.40	2.50	2.60
Q	5.60	5.80	6.00
S		6.15BSC	
R		0.50REF	
T	9.80	-	10.20
T1		1.65REF	
T2		8.00REF	
T3		12.80REF	
U	6.00	-	6.40
θ1	6°	7°	8°
θ2	4°	5°	6°
θ3	1°	-	1.5°
θ4	14°	15°	16°

Package Outline

TO-3P



COMMON DIMENSIONS

SYMBOL	MM		
	MIN	NOM	MAX
A	4.60	4.80	5.00
A1	1.40	1.50	1.60
A2	1.33	1.38	1.43
b	0.80	1.00	1.20
b1	2.80	3.00	3.20
b2	1.80	2.00	2.20
c	0.50	0.60	0.70
D	19.75	19.90	20.05
D1	13.70	13.90	14.10
D2	12.90REF		
E	15.40	15.60	15.80
E1	13.40	13.60	13.80
E2	9.40	9.60	9.80
e	5.45 TYP		
G	4.60	4.80	5.00
H	40.30	40.50	40.70
H1	23.20	23.40	23.60
h	0.05	0.10	0.15
L	7.40 TYP		
L1	9.00 TYP		
L2	11.00 TYP		
L3	1.00 REF		
ΦP	6.90	7.00	7.10
ΦP1	3.20 REF		
ΦP2	3.50 REF		
ΦP3	1.40	1.50	1.60
R	0.50 REF		
Q	5.00 REF		
Q1	12.56	12.76	12.96
U	7.8	8	8.2
θ1	5°	7°	9°
θ2	1°	3°	5°
θ3	60° REF		

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